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# Descriptors for Electron and Hole Charge Carriers in Metal Oxides

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## Supplementary Information

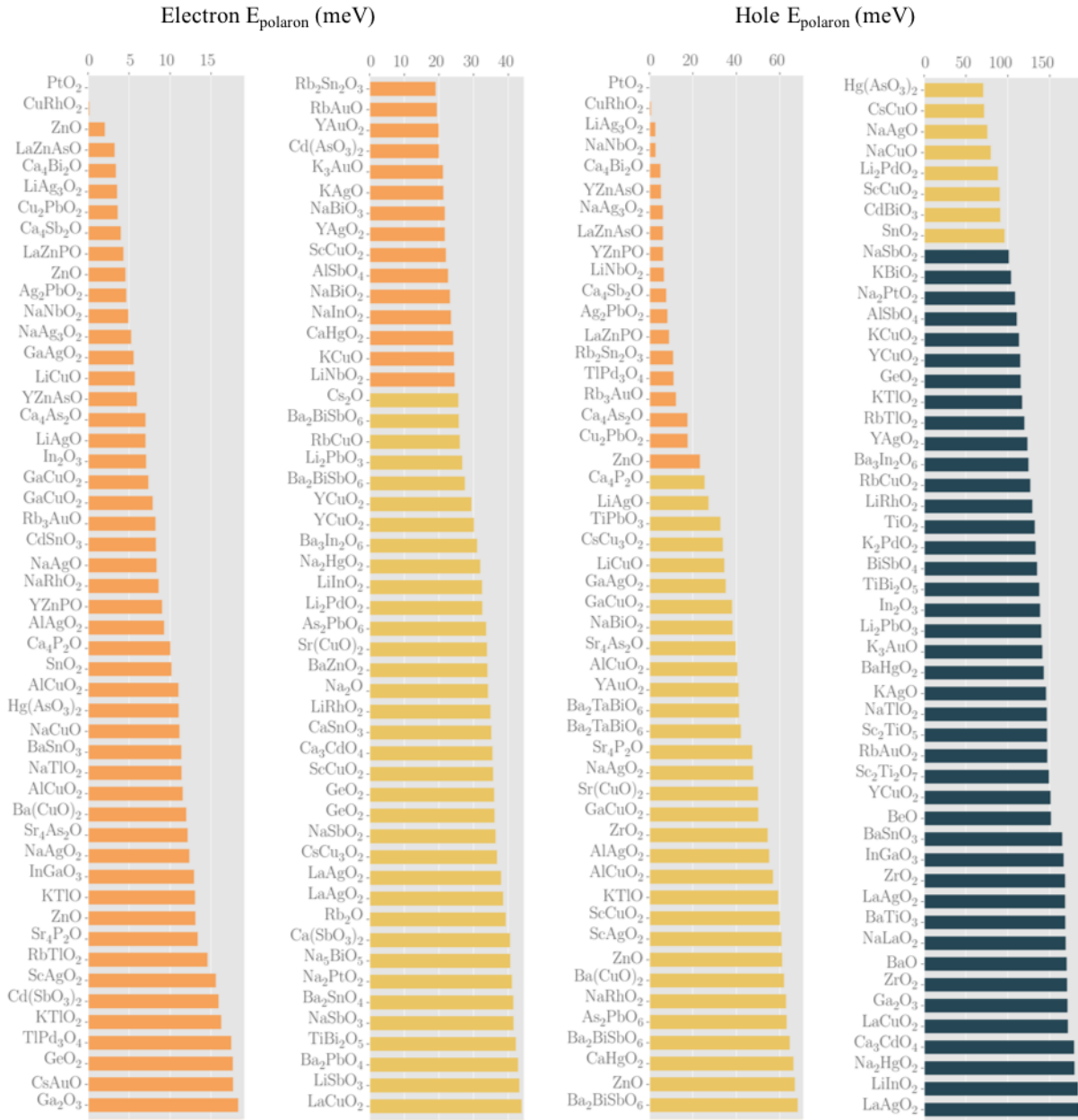


Figure S1: Electron and hole polaron binding energies calculated using the effective masses and dielectric constants from public data-sets. Some compositions have multiple entries due to polymorphism.

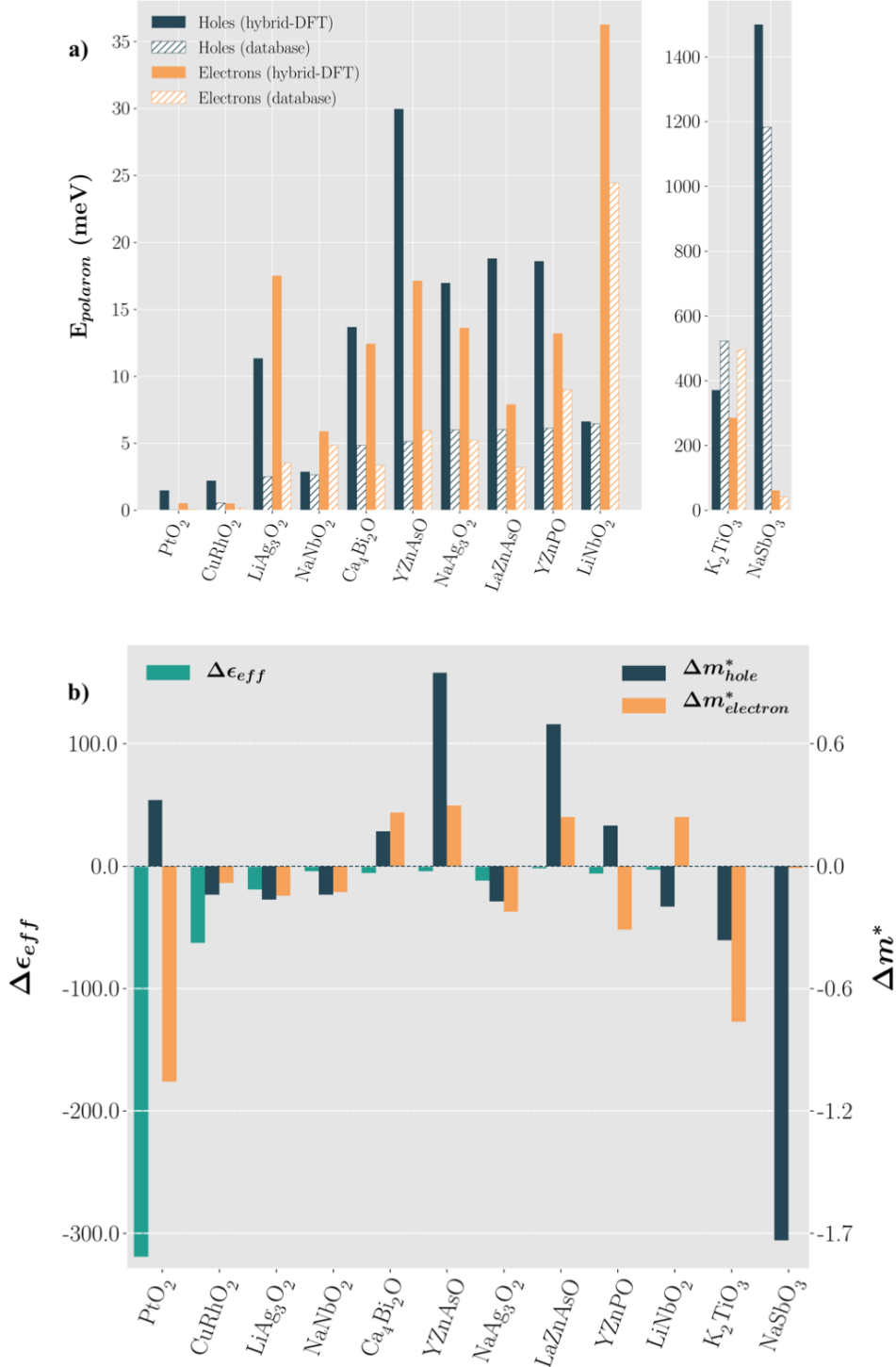


Figure S2: a) Polaron energy ( $E_{polaron}$ ) values as calculated using hybrid-DFT (solid bars) and database (hatched bars) for electrons (orange bars) and holes (blue bars). b) Absolute difference (database derived minus Hybrid-DFT derived) in  $\epsilon_{eff}$  (green bars) and effective mass ( $m^*$ ) for electrons (orange bars) and holes (blue bars).

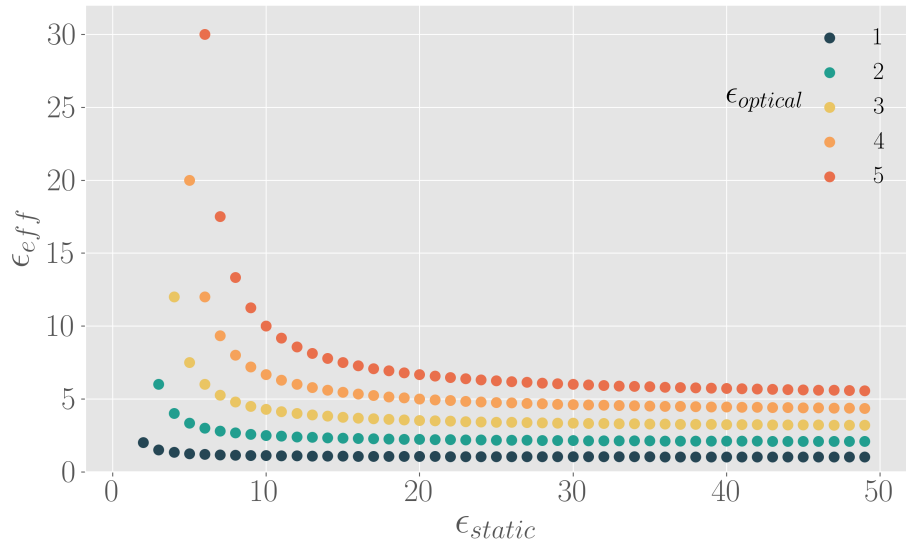


Figure S3: Visualization of the variation of  $\epsilon_{eff}$  (y-axis) with  $\epsilon_s$  (x-axis) at different fixed values of  $\epsilon_\infty$ . For  $\epsilon_s > 20$  the system is in a strong screening regime where  $\epsilon_{eff}$  shows little variation.